

SUBSTITUTE FORM PTO-1449 (MODIFIED)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. TPS/008	SERIAL NO. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary) (37 CFR 1.98(b))				APPLICANT Pradip K. Roy et al.	
				FILING DATE March 10, 2004	GROUP Unknown

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		PATENT NUMBER		ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A.A							
	A.B							
	A.C							
	A.D							
	A.E							
	A.F							
	A.G							
	A.H							
	A.I							
	A.J							
	A.K							

FOREIGN PATENTS OR PUBLISHED FOREIGN PATENT APPLICATIONS

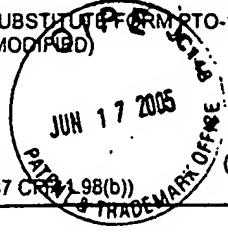
		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION (YES/NO)
<i>SKR</i>	A.L	EP0684650 B1	08/29/2001	EP	H01L	29/786	
	A.M						
	A.N						
	A.O						
	A.P						
	A.Q						

OTHER DOCUMENTS (Including Author, Title, Date, Place of Publication)

<i>SKR</i>	A.R	Stephen St. Onge and Mark Dupuis, <u>Innovations in Silicon Germanium Bicmos Processing</u> , Semiconductor Fabtech - 12th Edition, pp 195-199, published July, 2000.
	A.S	
	A.T	

EXAMINER	DATE CONSIDERED
<i>Stephen St. Onge</i>	10/13/05

EXAMINER: Initial if citation considered, whether or not in conformance. Draw line through citation only if not in conformance and not considered. Include a copy of this form with next communication to Applicant.

SUBSTITUTE FORM PTO-1449 (MODIFIED)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. TPS-008	SERIAL NO. 10/797,425
 <small>(37 CFR 1.98(b))</small>		INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANT Pradip K. Roy et al.	
		(Use several sheets if necessary)		FILING DATE March 10, 2004	GROUP 2811

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		PATENT NUMBER							ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>SPR</i>	A.A	6	4	2	3	6	3	2	07/23/2002	Samavedam et al.	438	652	07/21/2000
	A.B												
	A.C												
	A.D												
	A.E												
	A.F												
	A.G												
	A.H												
	A.I												
	A.J												
	A.K												

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		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION (YES/NO)
	A.L						
	A.M						
	A.N						
	A.O						
	A.P						
	A.Q						

OTHER DOCUMENTS (Including Author, Title, Date, Place of Publication)

<i>SPR</i>	A.R	Luo et al., <u>Seedless Method of Forming a Silicon Germanium Layer on a Gate Dielectric Layer</u> , US 2004/0009680 A1; publication date 01/15/2004; filed 07/10/2002; U.S. Class 438/933
<i>SPR</i>	A.S	Uejima et al., <u>Highly Reliable Poly-SiGe/Amorphous-Si Gate CMOS</u> , Electron Devices Meeting; IEDM Technical Digest; pp. 445-448; 12/10/2000
	A.T	

EXAMINER	DATE CONSIDERED
<i>SPR</i>	01/13/05

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